



N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	1.7mΩ @ V _{GS} = 10V	100A
30V	2.4mΩ @ V _{GS} = 4.5V	80A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

PowerDI5060-8

- Backlighting
- Power Management Functions
- **DC-DC Converters**

Features and Benefits

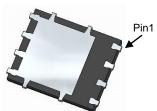
- Low R_{DS(ON)} Minimizes On-State Losses
- Excellent Q_{gd} x R_{DS(ON)} Product (FOM)
- Advanced Technology for DC-DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- 100% Unclamped Inductive Switching Ensures More Reliability
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

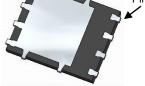
Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)

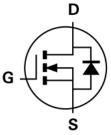








Bottom View



D sl Пο Пο s[Пρ GΪ Top View

Internal Schematic Pin Configuration

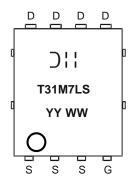
Ordering Information (Note 4)

Part Number	Case	Packaging
DMT31M7LPS-13	PowerDI5060-8	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



) | | = Manufacturer's Marking T31M7LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	30	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current, V _{GS} = 10V (Note 6)	$T_A = +25$ °C $T_A = +70$ °C	I _D	30 24	Α
Continuous Drain Current, V _{GS} = 10V (Note 7)	$T_C = +25$ °C $T_C = +70$ °C	I _D	100 80	Α
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	2.8	Α	
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I _{DM}	400	Α	
Pulsed Body Diode Forward Current (380µs Pulse, Duty Cycl	I _{SM}	400	Α	
Avalanche Current, L=0.1mH (Note 8)	I _{AS}	65	Α	
Avalanche Energy, L=0.1mH (Note 8)	E _{AS}	215	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	1.3	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	94	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.4	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	52	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	P _D	113	W
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	1.1	°C/W
Operating and Storage Temperature Range		$T_{J_{I}}T_{STG}$	-55 to +150	°C

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = 20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)			•	•		
Gate Threshold Voltage	V _{GS(TH)}	1.0	_	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance	В	_	1.3	1.7	0	$V_{GS} = 10V, I_D = 20A$
Static Diani-Source On-Resistance	R _{DS(ON)}	_	1.9	2.4	mΩ	$V_{GS} = 4.5V, I_D = 20A$
Diode Forward Voltage	V _{SD}	_	0.7	1.0	V	$V_{GS} = 0V$, $I_S = 2A$
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	_	5741	_		V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	Coss	_	2119	_	pF	
Reverse Transfer Capacitance	C _{rss}	_	424	_		
Gate Resistance	Rq	_	1.5	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Qq	_	90	_		
Total Gate Charge (V _{GS} = 4.5V)	Qq	_	45	_	0	45)/ 1 004
Gate-Source Charge	Q _{gs}	_	11.6	_	nC	$V_{DD} = 15V, I_D = 20A$
Gate-Drain Charge	Q_{gd}	_	21.6	_		
Turn-On Delay Time	t _{D(ON)}	_	6.9	_		$V_{DD} = 15V, V_{GS} = 10V,$ $R_g = 3\Omega, I_D = 20A$
Turn-On Rise Time	t _R	_	16.5	_		
Turn-Off Delay Time	t _{D(OFF)}		49.6	_	ns	
Turn-Off Fall Time	t _F	_	34.5	_		
Reverse Recovery Time	t _{RR}		32.5	_	ns	$I_F = 15A$, $dI/dt = 500A/\mu s$
Reverse Recovery Charge	Q_{RR}	_	55	_	nC	I _F = 15A, dl/dt = 500A/μs

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

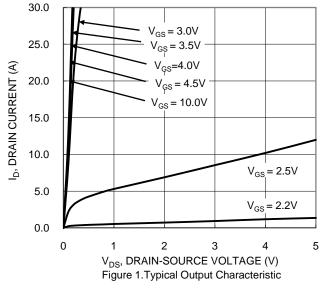
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

^{8.} I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25$ °C.

^{9.} Short duration pulse test used to minimize self-heating effect.

^{10.} Guaranteed by design. Not subject to product testing.





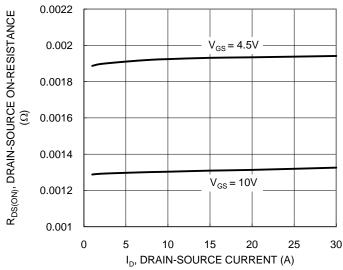


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

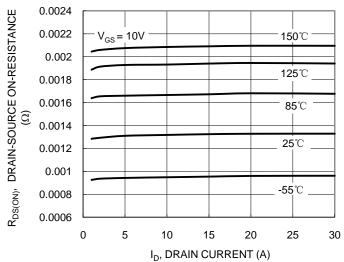


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

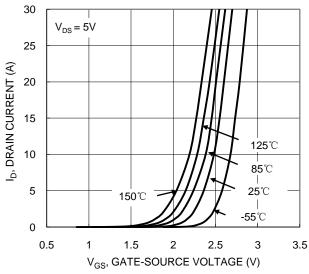


Figure 2. Typical Transfer Characteristic

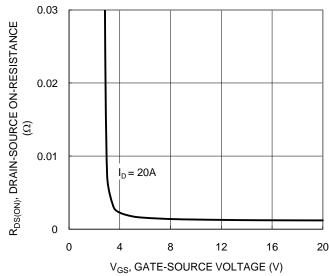


Figure 4. Typical Transfer Characteristic

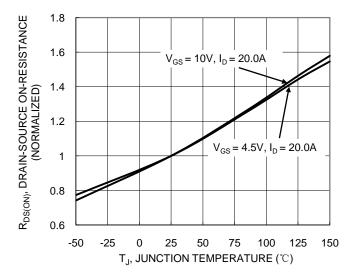


Figure 6. On-Resistance Variation with Junction Temperature



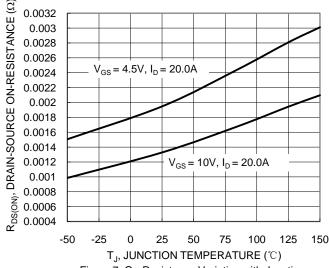
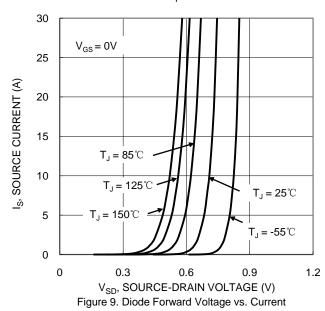


Figure 7. On-Resistance Variation with Junction Temperature



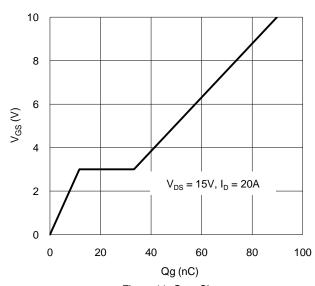


Figure 11. Gate Charge

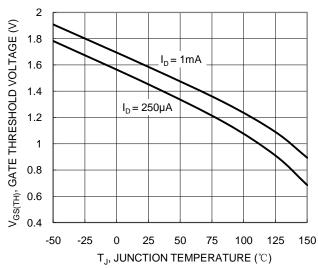
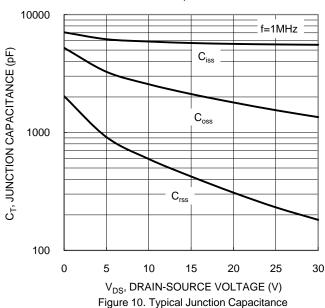


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 R_{DS(ON)} Limited 100 ID, DRAIN CURRENT (A) 10 P_W =1s $T_{J(Max)} = 150^{\circ}C$ $T_C = 25^{\circ}C$ Single Pulse $P_W = 10s$ DUT on Infinite Heatsink DC $V_{GS} = 10V$ 0.1 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



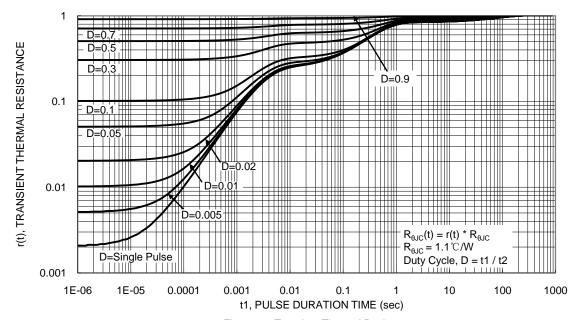


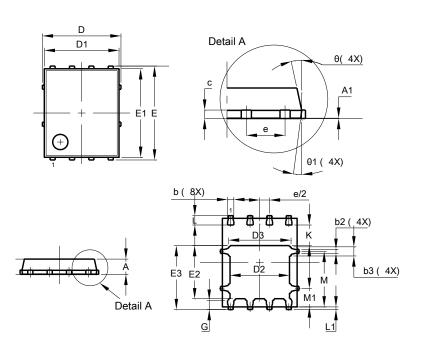
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8

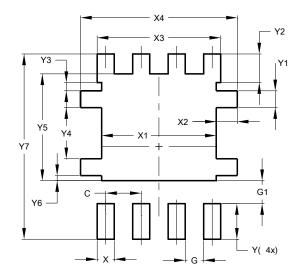


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
C	0.230	0.330	0.277		
D	,	5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(6.15 BSC	}		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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